

**80V, 229A, 1.3mΩ N-channel Power SGT MOSFET**
**JMSH0802PTL**
**Features**

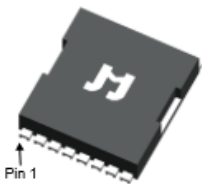
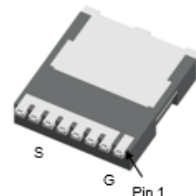
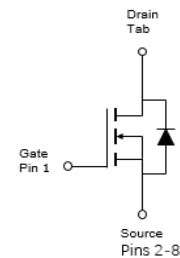
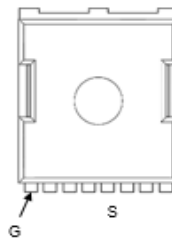
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- 100% UIS Tested
- 100%  $\Delta V_{ds}$  Tested
- Halogen-free; RoHS-compliant
- Pb-free plating

**Applications**

- Load Switch
- PWM Application
- Power Management

**Product Summary**

Parameters	Value	Unit
$V_{DSS}$	80	V
$V_{GS(th\_Typ)}$	2.9	V
$I_D(@V_{GS}=10V)$	229	A
$R_{DS(ON)\_Typ}(@V_{GS}=10V)$	1.3	mΩ


**PowerJE®10x12**

**Pin Assignment**

**Schematic Diagram**
**Ordering Information**

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH0802PTL	SH0802P	1	Tape&Reel	PowerJE®10x12	2000	10000

**Absolute Maximum Ratings** (@  $T_C = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-to-Source Voltage	80	V
$V_{GS}$	Gate-to-Source Voltage	±20	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ\text{C}$	229
		$T_C = 100^\circ\text{C}$	145
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>	Refer to Fig.4	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(2)</sup>	900	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	357
		$T_C = 100^\circ\text{C}$	143
$T_J, T_{STG}$	Junction & Storage Temperature Range	-55 to 150	°C

**Thermal Characteristics**

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(3)</sup>	34	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	80	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 64\text{V}$ , $V_{GS} = 0\text{V}$	-	-	1.0	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$ , $V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	2.1	2.9	4.1	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance <sup>(4)</sup>	$V_{GS} = 10\text{V}$ , $I_D = 15\text{A}$	-	1.3	1.8	m $\Omega$
<b>Dynamic Characteristics</b>						
$R_g$	Gate Resistance	$f = 1\text{MHz}$	-	0.8	-	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$ , $V_{DS} = 40\text{V}$ , $f = 1\text{MHz}$	4569	6396	8635	pF
$C_{oss}$	Output Capacitance		874	1224	1652	pF
$C_{rss}$	Reverse Transfer Capacitance		17	23	32	pF
$Q_g$	Total Gate Charge	$V_{GS} = 0$ to $10\text{V}$ $V_{DS} = 40\text{V}$ , $I_D = 20\text{A}$	65	91	123	nC
$Q_{gs}$	Gate Source Charge		23	33	44	nC
$Q_{gd}$	Gate Drain("Miller") Charge		13	18	24	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}$ , $V_{DD} = 40\text{V}$ $I_D = 20\text{A}$ , $R_{GEN} = 6.2\Omega$	-	31	-	ns
$t_r$	Turn-On Rise Time		-	35	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	61	-	ns
$t_f$	Turn-Off Fall Time		-	31	-	ns
<b>Body Diode Characteristics</b>						
$I_S$	Maximum Continuous Body Diode Forward Current		-	-	229	A
$I_{SM}$	Maximum Pulsed Body Diode Forward Current		-	-	917	A
$V_{SD}$	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_S = 15\text{A}$	-		1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = 20\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$	54	75	101	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	155	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2.  $E_{AS}$  condition: Starting  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = 40\text{V}$ ,  $V_G = 10\text{V}$ ,  $R_G = 25\text{ohm}$ ,  $L = 3\text{mH}$ ,  $I_{AS} = 24.5\text{A}$ ,  $V_{DD} = 0\text{V}$  during time in avalanche.
  3.  $R_{\theta JA}$  is measured with the device mounted on a  $1\text{inch}^2$  pad of 2oz copper FR4 PCB.
  4. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$ .



## Typical Performance Characteristics

Figure 1: Power De-rating

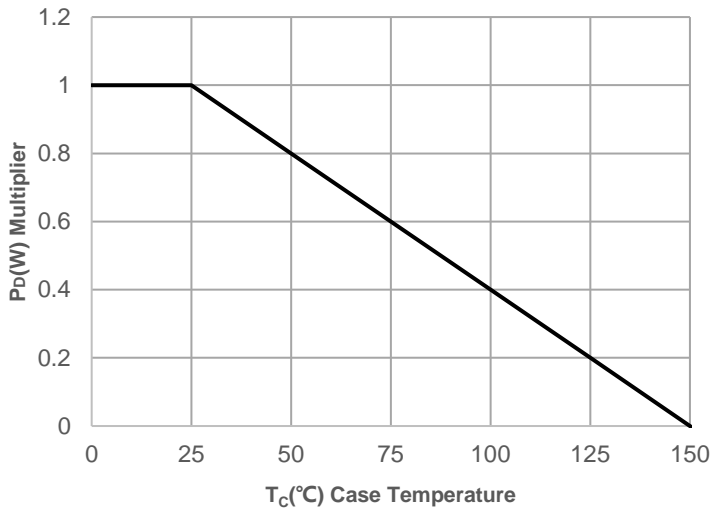


Figure 2: Current De-rating

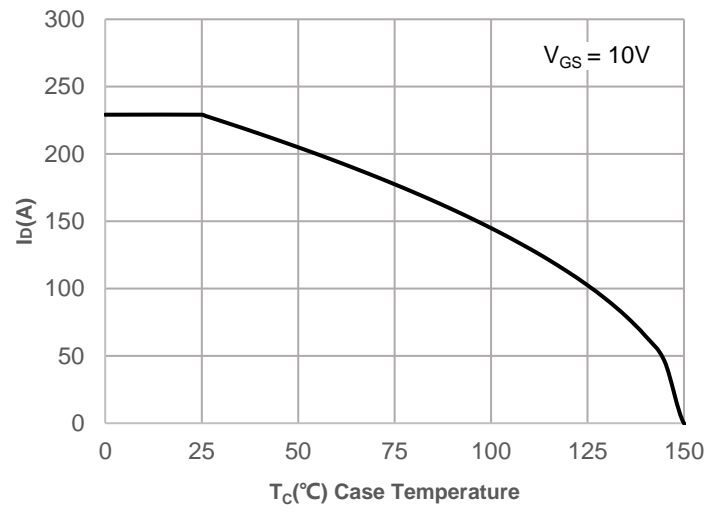


Figure 3: Normalized Maximum Transient Thermal Impedance

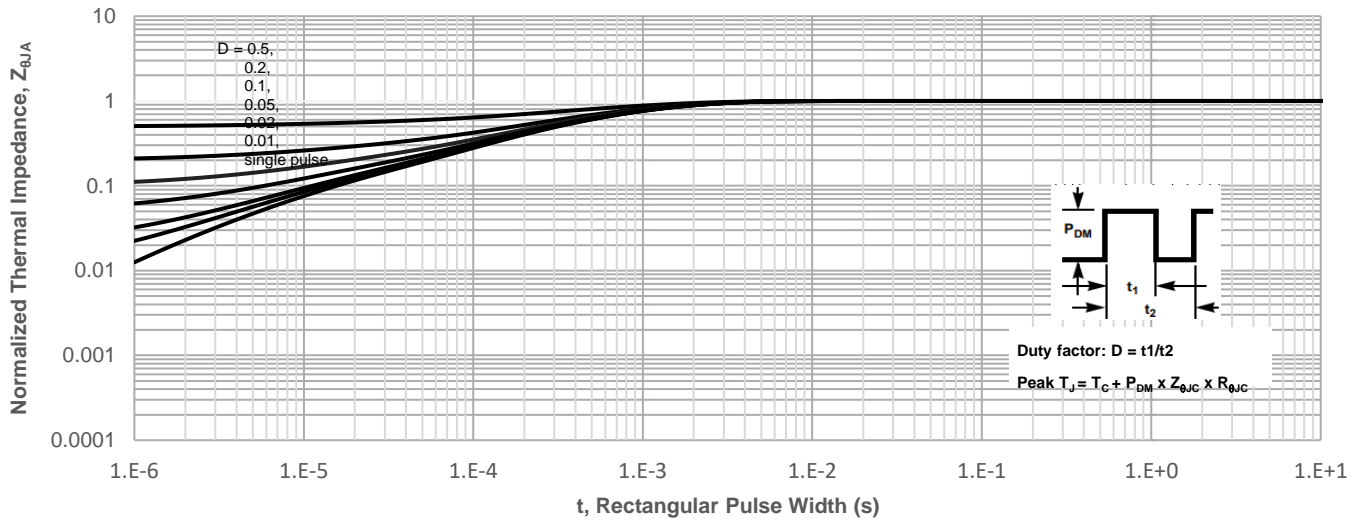
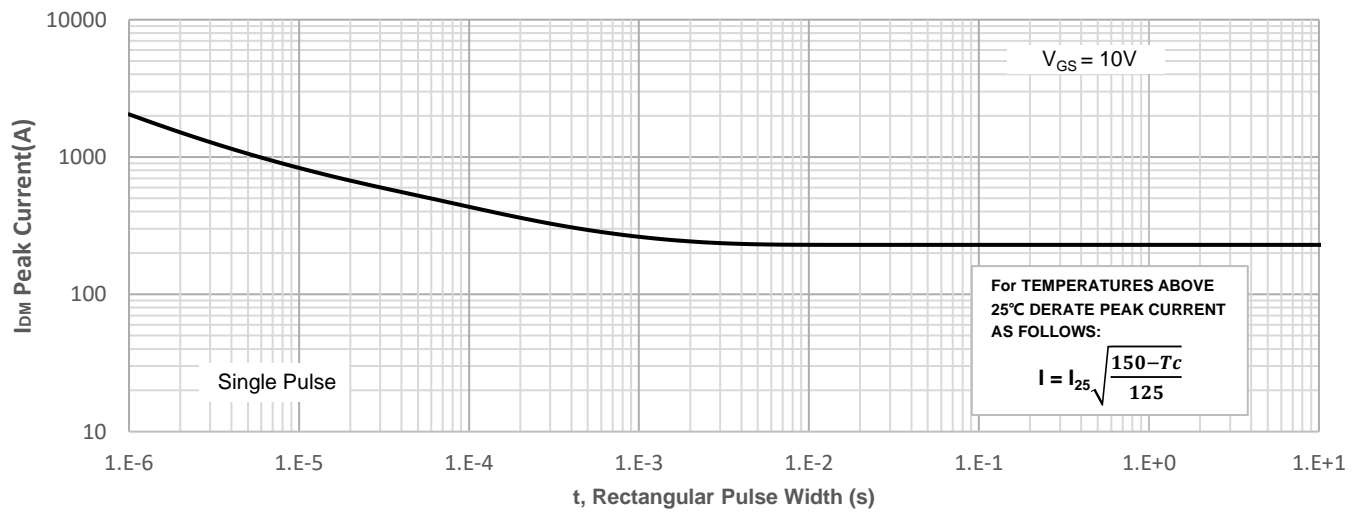


Figure 4: Peak Current Capacity



## Typical Performance Characteristics

Figure 5: Output Characteristics

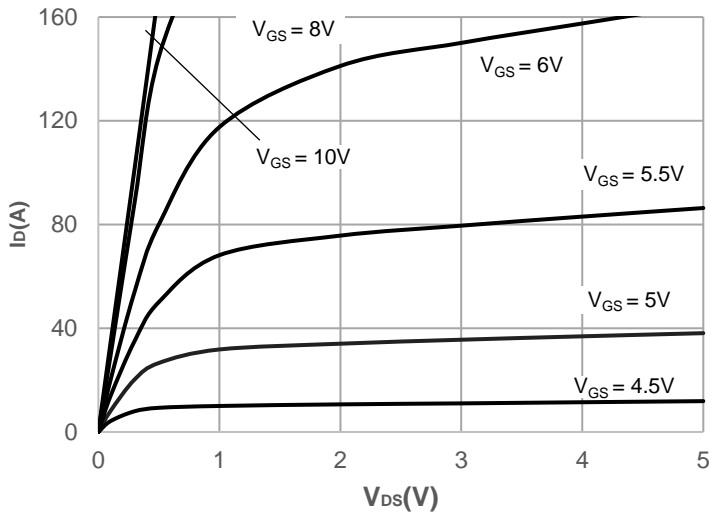


Figure 6: Typical Transfer Characteristics

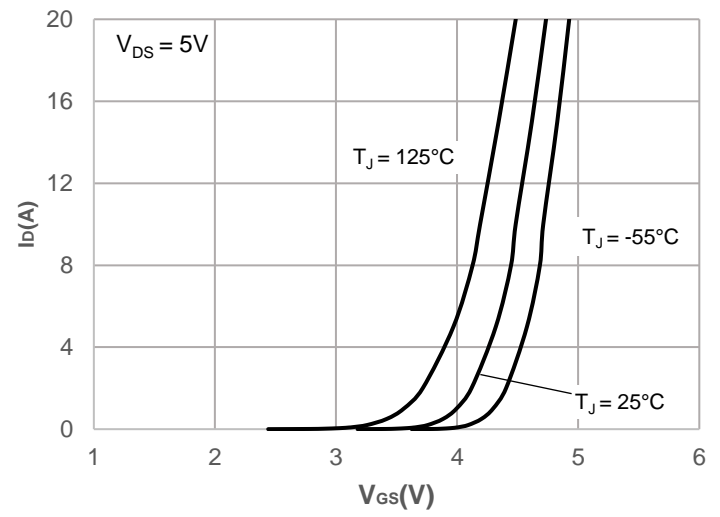


Figure 7: On-resistance vs. Drain Current

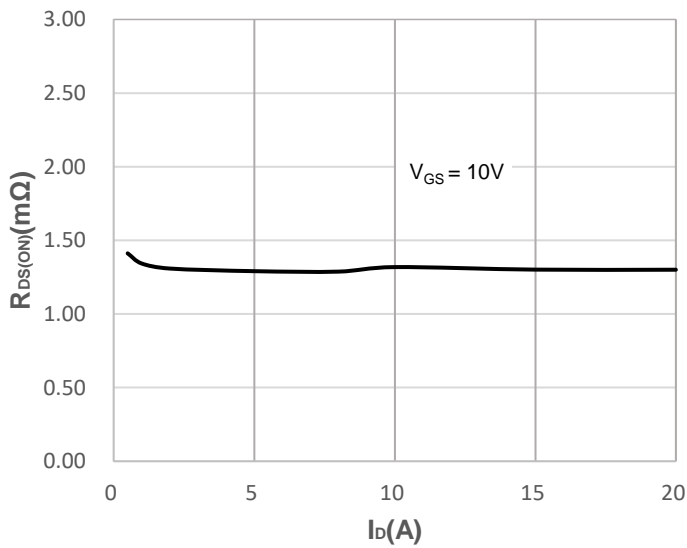


Figure 8: Body Diode Characteristics

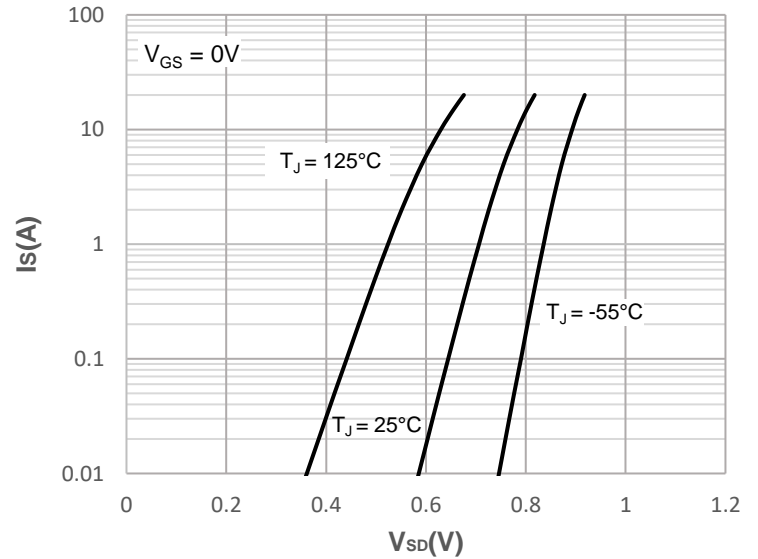


Figure 9: Gate Charge Characteristics

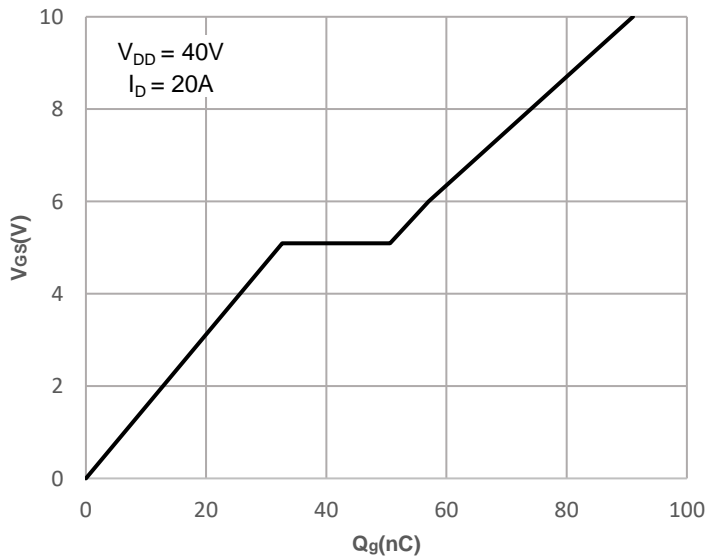
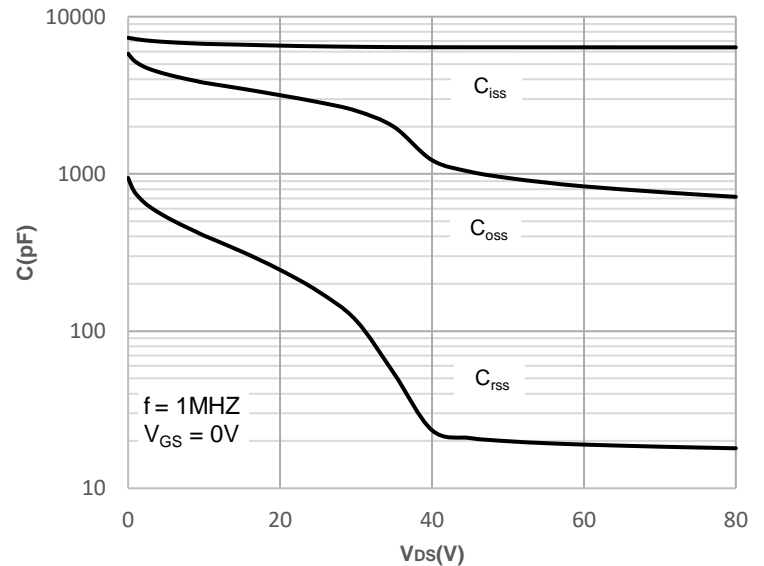


Figure 10: Capacitance Characteristics



## Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

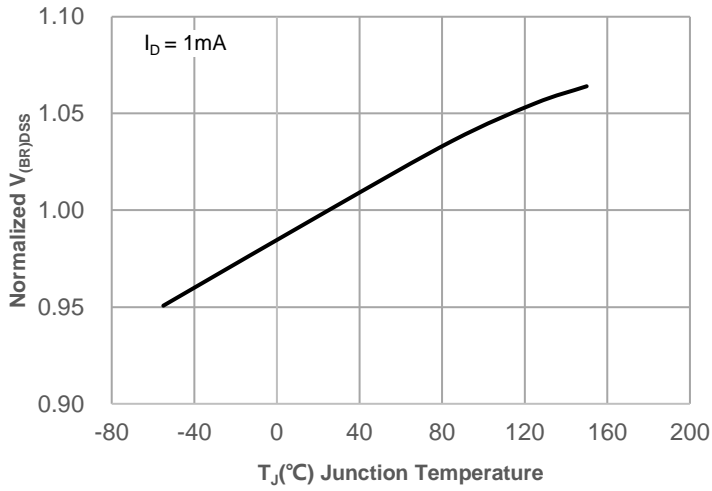


Figure 12: Normalized on Resistance vs. Junction Temperature

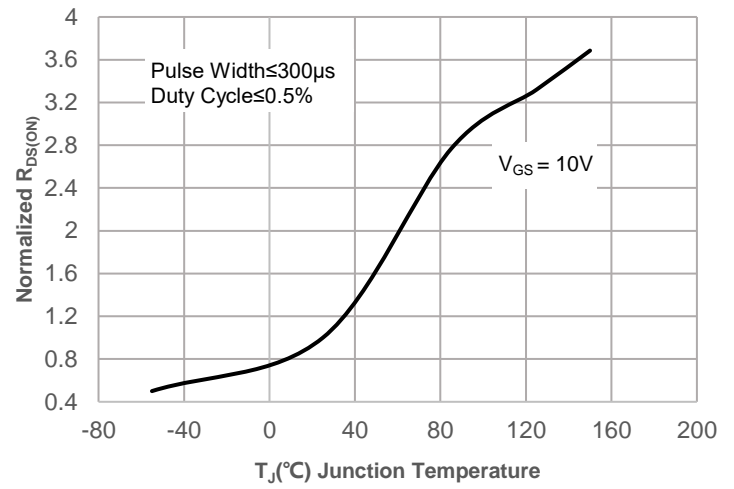


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

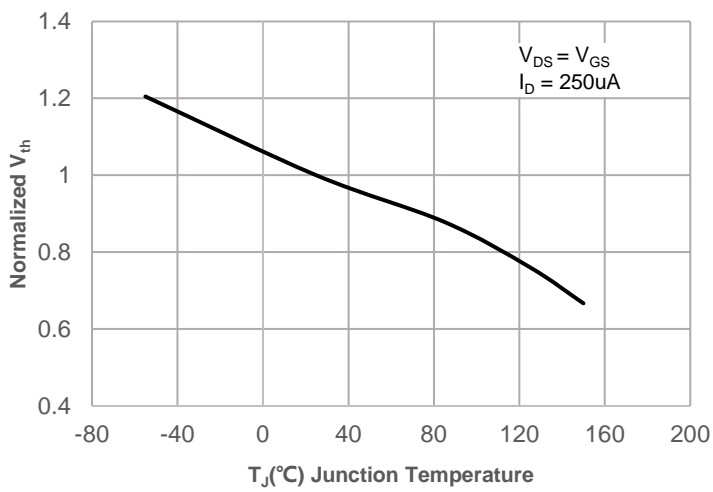


Figure 14:  $R_{DS(ON)}$  vs.  $V_{GS}$

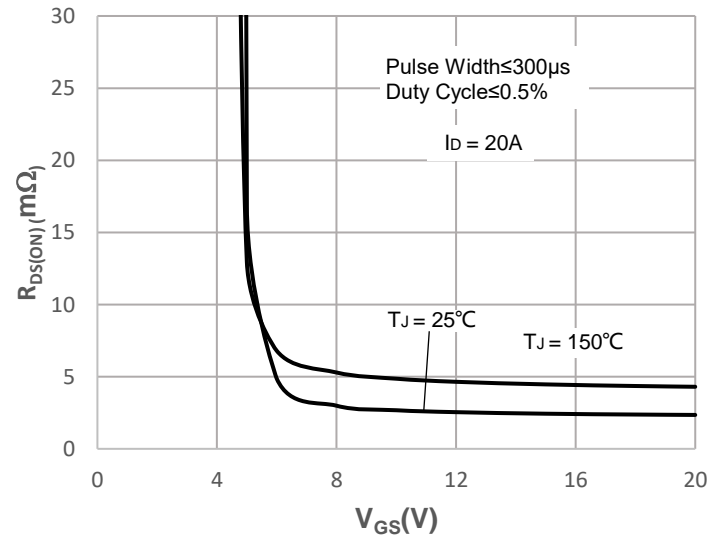
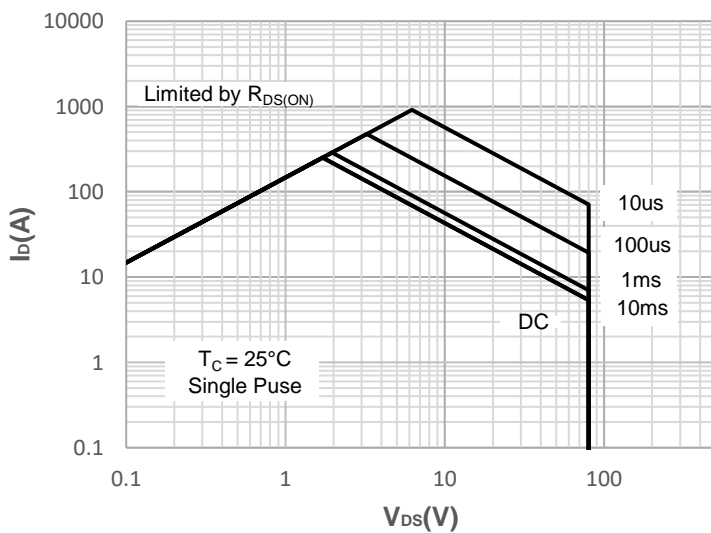


Figure 15: Maximum Safe Operating Area



### Test Circuit

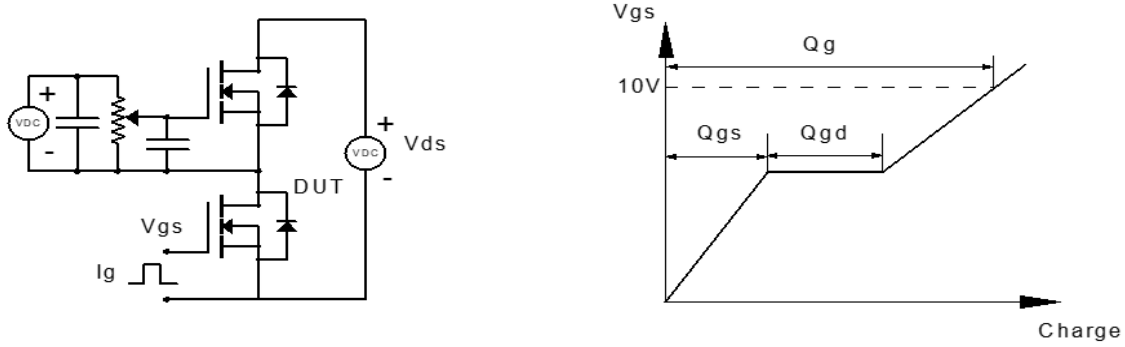


Figure 1: Gate Charge Test Circuit & Waveform

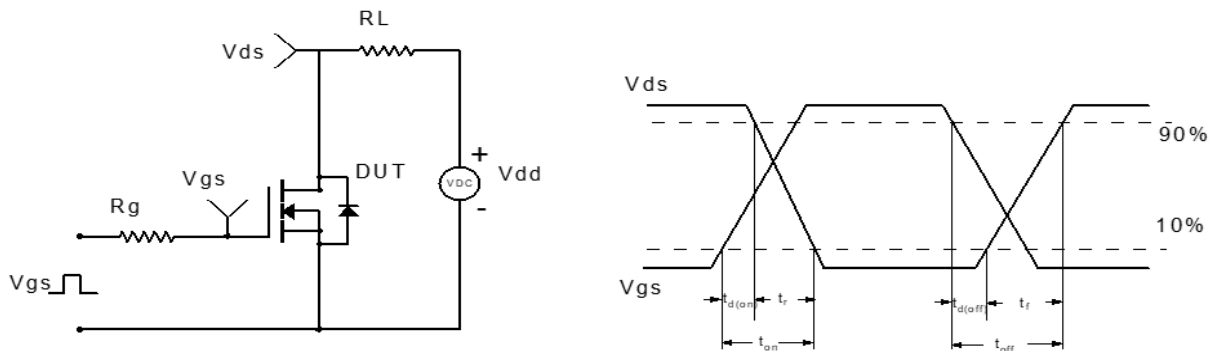


Figure 2: Resistive Switching Test Circuit & Waveform

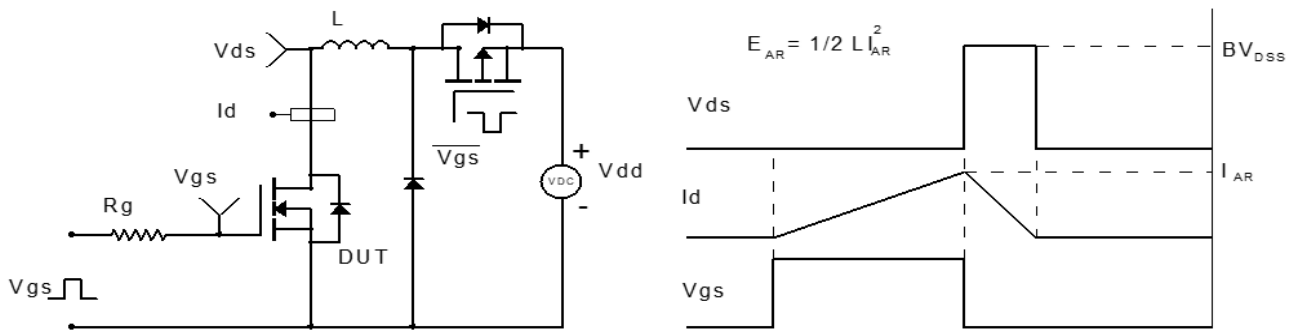


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

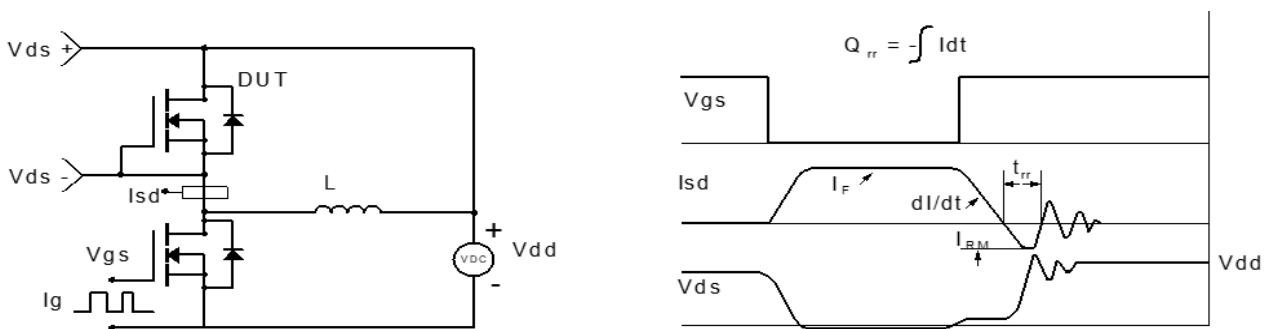
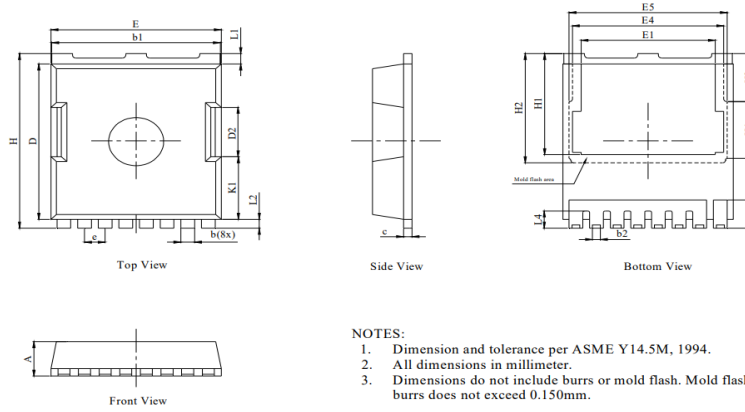


Figure 4: Diode Recovery Test Circuit & Waveform



## Package Mechanical Data(PowerJE®10x12)

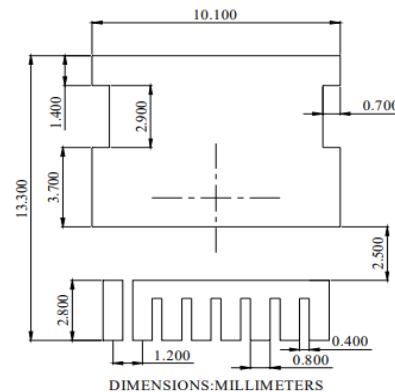
Package Outlines



- NOTES:
1. Dimension and tolerance per ASME Y14.5M, 1994.
  2. All dimensions in millimeter.
  3. Dimensions do not include burrs or mold flash. Mold flash or burrs does not exceed 0.150mm.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.42	0.46	0.50
c	0.40	0.50	0.60
D	10.28	10.38	10.58
D2		3.30	
E	9.70	9.90	10.10
E1		7.80	
E4		8.80	
E5		9.20	
e	1.20 (BSC)		
H	11.48	11.68	11.88
H1	6.55	6.75	6.85
H2		7.30	
H3		3.20	
H4		3.80	
K1		4.18	
L	1.70	1.90	2.10
L1		0.70	
L2		0.60	
L4	1.00	1.15	1.30

Recommended Soldering Footprint



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